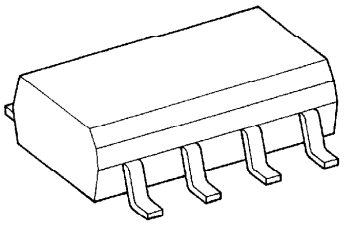
TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7W08F, TC7W08FU

DUAL 2-INPUT AND GATE

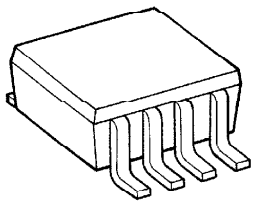
The TC7W08 is a high speed C^2MOS 2-INPUT AND GATE fabricated with silicon gate C^2MOS technology.
It achives the high speed operation similar to equivalent LSTTL while maintaining the C^2MOS low power dissipation.
The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

TC7W08F



SOP8-P-1.27

TC7W08FU



SSOP8-P-0.65

Weight SOP8-P-1.27 : 0.05g (Typ.)
SSOP8-P-0.65 : 0.02g (Typ.)

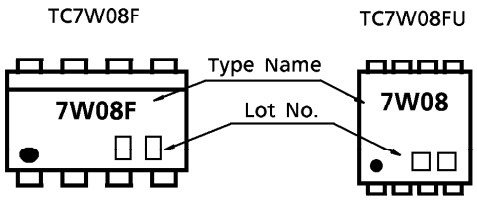
FEATURES

- High Speed ..... t_{pd} = 6ns (Typ.) at V_{CC} = 5V
- Low Power Dissipation ..... I_{CC} = 1μA (Max.) at Ta = 25°C
- High Noise Immunity ..... $V_{NIH} = V_{NIL}$ = 28% V_{CC} (Min.)
- Output Drive Capability ..... 10 LSTTL Loads
- Symmetrical Output Impedance ... $|I_{OH}| = I_{OL}$ = 4mA (Min.)
- Balanced Propagation Delays ..... $t_{pLH} \fallingdotseq t_{pHL}$
- Wide Operating Voltage Range ... $V_{CC\,(opr)}$ = 2~6V

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	−0.5~7	V
DC Input Voltage	V_{IN}	−0.5~V_{CC} + 0.5	V
DC Output Voltage	V_{OUT}	−0.5~V_{CC} + 0.5	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} / Ground Current	I_{CC}	± 25	mA
Power Dissipation	P_D	300	mW
Storage Temperature	T_{stg}	−65~150	°C
Lead Temperature (10s)	T_L	260	°C

MARKING



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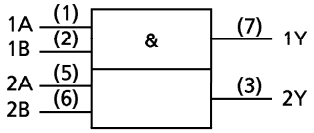
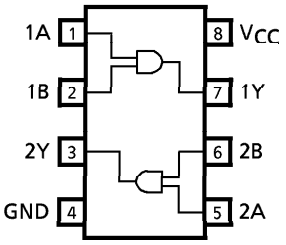
LOGIC DIAGRAM



TRUTH TABLE

A	B	Y
L	L	L
L	H	L
H	L	L
H	H	H

PIN ASSIGNMENT (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~V_{CC}	V
Output Voltage	V_{OUT}	0~V_{CC}	V
Operating Temperature	T_{opr}	−40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 (V_{CC} = 2.0V) 0~ 500 (V_{CC} = 4.5V) 0~ 400 (V_{CC} = 6.0V)	ns

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION		Ta = 25°C				Ta = −40~85°C		UNIT
				V_{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	
High-Level Input Voltage	V_{IH}	—		2.0	1.5	—	—	1.5	—	V
				4.5	3.15	—	—	3.15	—	
				6.0	4.2	—	—	4.2	—	
Low-Level Input Voltage	V_{IL}	—		2.0	—	—	0.5	—	0.5	V
				4.5	—	—	1.35	—	1.35	
				6.0	—	—	1.8	—	1.8	
High-Level Output Voltage	V_{OH}	V_{IN} = V_{IH}	I_{OH} = −20μA	2.0	1.9	2.0	—	1.9	—	V
				4.5	4.4	4.5	—	4.4	—	
				6.0	5.9	6.0	—	5.9	—	
			I_{OH} = −4mA	4.5	4.18	4.31	—	4.13	—	
			I_{OH} = −5.2mA	6.0	5.68	5.80	—	5.63	—	
Low-Level Output Voltage	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 20μA	2.0	—	0.0	0.1	—	0.1	V
				4.5	—	0.0	0.1	—	0.1	
				6.0	—	0.0	0.1	—	0.1	
			I_{OL} = 4mA	4.5	—	0.17	0.26	—	0.33	
			I_{OL} = 5.2mA	6.0	—	0.18	0.26	—	0.33	
Input Leakage Current	I_{IN}	V_{IN} = V_{CC} or GND		6.0	—	—	±0.1	—	±1.0	μA
Quiescent Supply Current	I_{CC}	V_{IN} = V_{CC} or GND		6.0	—	—	1.0	—	10.0	

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AC ELECTRICAL CHARACTERISTICS (C_L = 15pF, V_{CC} = 5V, Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta = 25°C			UNIT
			MIN.	TYP.	MAX.	
Output Transition Time	t_{TLH} t_{THL}	—	—	4	8	ns
Propagation Delay Time	t_{pLH} t_{pHL}	—	—	6	12	ns

AC ELECTRICAL CHARACTERISTICS (C_L = 50pF, Input $t_r = t_f$ = 6ns)

CHARACTERISTIC	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = −40~85°C		UNIT
			V_{CC}	MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{TLH} t_{THL}	—	2.0	—	25	75	—	95	ns
			4.5	—	7	15	—	19	
			6.0	—	6	13	—	16	
Propagation Delay Time	t_{pLH} t_{pHL}	—	2.0	—	27	75	—	95	ns
			4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Input Capacitance	C_{IN}	—		—	5	10	—	10	pF
Power Dissipation Capacitance	C_{PD}	(Note 1)		—	19	—	—	—	

Note 1 : C_{PD} is defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

Average operating current can be obtained by the equation hereunder.

$I_{CC\,(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 2$ (per gate)